Schematic Diagram Use of Flowable Oxides for Mesa Gap Fill and Planarization of AlGaN/GaN HEMT Devices

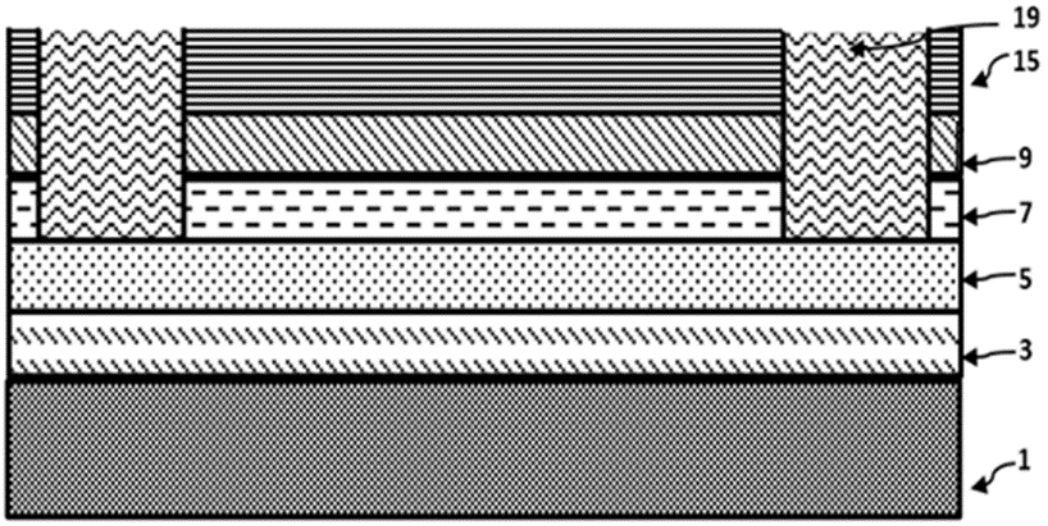

Figure 1: GaN/AlGaN HEMT planarized structure with flowable oxide

1 : Si (111)
3 : Buffer layer
5 : Undoped GaN
7 : GaN channel
9: AlGaN Barrier
15: Passivation
17: Photoresist
19: Flowable oxide